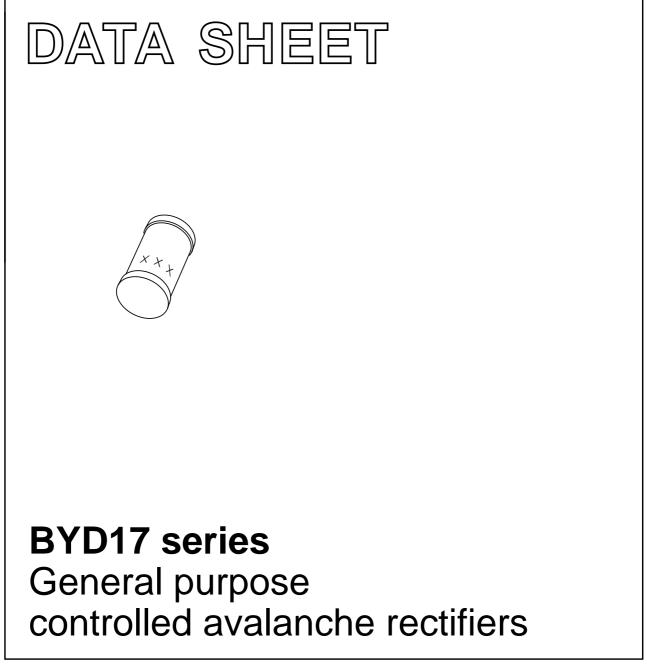
## DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 Nov 11 2001 Oct 26



## General purpose controlled avalanche rectifiers

### FEATURES

- · Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier outline.

#### DESCRIPTION

Cavity free cylindrical glass package through Implotec<sup>TM(1)</sup> technology.

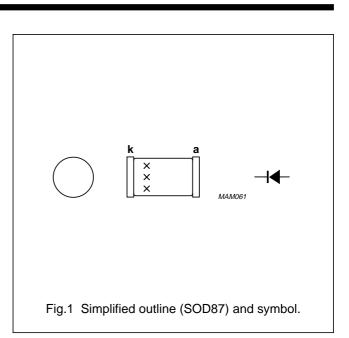
This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                       | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|---------------------------------|------------|------|------|------|
| V <sub>RRM</sub> | repetitive peak reverse voltage |            |      |      |      |
|                  | BYD17D                          |            | _    | 200  | V    |
|                  | BYD17G                          |            | _    | 400  | V    |
|                  | BYD17J                          |            | _    | 600  | V    |
|                  | BYD17K                          |            | _    | 800  | V    |
|                  | BYD17M                          |            | _    | 1000 | V    |
| V <sub>RWM</sub> | crest working reverse voltage   |            |      |      |      |
|                  | BYD17D                          |            | _    | 200  | V    |
|                  | BYD17G                          |            | _    | 400  | V    |
|                  | BYD17J                          |            | _    | 600  | V    |
|                  | BYD17K                          |            | -    | 800  | V    |
|                  | BYD17M                          |            | -    | 1000 | V    |
| V <sub>R</sub>   | continuous reverse voltage      |            |      |      |      |
|                  | BYD17D                          |            | _    | 200  | V    |
|                  | BYD17G                          |            | _    | 400  | V    |
|                  | BYD17J                          |            | _    | 600  | V    |
|                  | BYD17K                          |            | _    | 800  | V    |
|                  | BYD17M                          |            | _    | 1000 | V    |



## General purpose controlled avalanche rectifiers

## BYD17 series

| SYMBOL             | PARAMETER                                       | CONDITIONS   | MIN. | MAX. | UNIT |
|--------------------|---|--|------|------|------|
| I <sub>F(AV)</sub> | average forward current                         | T <sub>tp</sub> = 105 °C;<br>averaged over any 20 ms period;<br>see Figs 2 and 4                       | _    | 1.5  | A    |
|                    |   | $T_{amb}$ = 65 °C; PCB mounting (see<br>Fig.9);<br>averaged over any 20 ms period;<br>see Figs 3 and 4 | _    | 0.6  | A    |
| I <sub>FSM</sub>   | non-repetitive peak forward current             | t = 10 ms half sinewave;<br>$T_j = T_{j max}$ prior to surge;<br>$V_R = V_{RRMmax}$                    | _    | 20   | A    |
| E <sub>RSM</sub>   | non-repetitive peak reverse avalanche<br>energy | L = 120 mH; $T_j = T_{j max}$ prior to<br>surge; inductive load switched off                           | _    | 7    | mJ   |
| T <sub>stg</sub>   | storage temperature                             |  | -65  | +175 | °C   |
| Tj                 | junction temperature                            | see Fig.5  | -65  | +175 | °C   |

### ELECTRICAL CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

| SYMBOL             | PARAMETER                              | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|--------------------|--|--|------|------|------|------|
| V <sub>F</sub>     | forward voltage                        | $I_F = 1 \text{ A}; T_j = T_{j \text{ max}}; \text{see Fig.6}$                             | _    | _    | 0.93 | V    |
|                    |  | I <sub>F</sub> = 1 A; see Fig.6  | _    | _    | 1.05 | V    |
| V <sub>(BR)R</sub> | reverse avalanche<br>breakdown voltage | I <sub>R</sub> = 0.1 mA  |      |      |      |      |
|                    | BYD17D                                 |  | 225  | _    | _    | V    |
|                    | BYD17G                                 |  | 450  | _    | _    | V    |
|                    | BYD17J                                 |  | 650  | _    | _    | V    |
|                    | BYD17K                                 |  | 900  | _    | _    | V    |
|                    | BYD17M                                 |  | 1100 | _    | -    | V    |
| I <sub>R</sub>     | reverse current                        | V <sub>R</sub> = V <sub>RRMmax</sub> ; see Fig.7   | _    | _    | 1    | μA   |
|                    |  | $V_R = V_{RRMmax}$ ; $T_j = 165 \text{ °C}$ ; see Fig.7                                    | _    | _    | 100  | μA   |
| t <sub>rr</sub>    | reverse recovery time                  | when switched from $I_F = 0.5$ A to $I_R = 1$ A;<br>measured at $I_R = 0.25$ A; see Fig.10 | _    | 3    | _    | μs   |
| C <sub>d</sub>     | diode capacitance                      | $V_R = 0 V$ ; f = 1 MHz; see Fig.8   | _    | 21   | _    | pF   |

### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                     | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R <sub>th j-tp</sub> | thermal resistance from junction to tie-point |            | 30    | K/W  |
| R <sub>th j-a</sub>  | thermal resistance from junction to ambient   | note 1     | 150   | K/W  |

### Note

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper ≥40 μm, see Fig.9. For more information please refer to the *"General Part of associated Handbook"*.

## General purpose controlled avalanche rectifiers

## **BYD17** series

### **GRAPHICAL DATA**

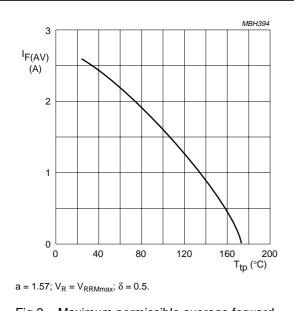


Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

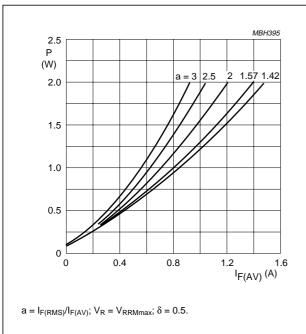


Fig.4 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

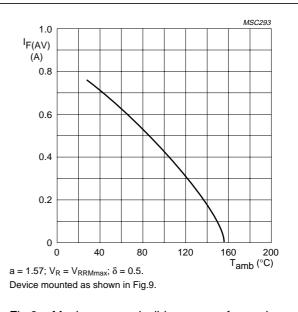
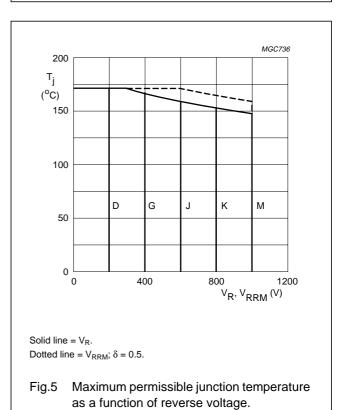
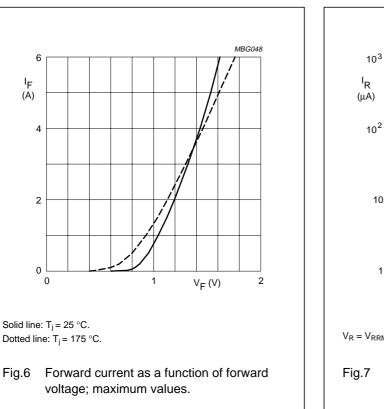


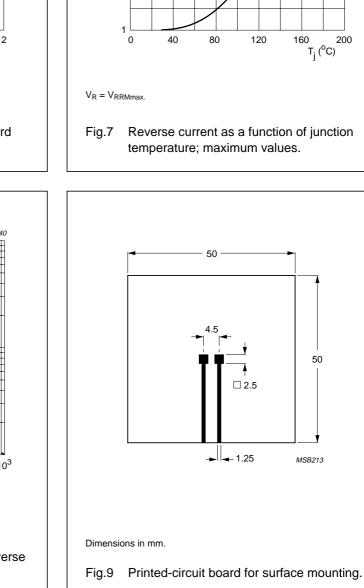
Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

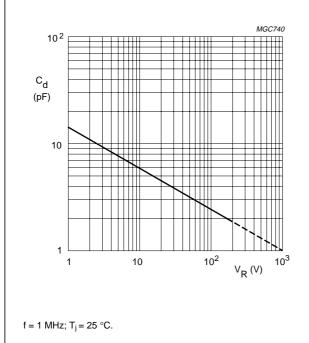


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## General purpose controlled avalanche rectifiers

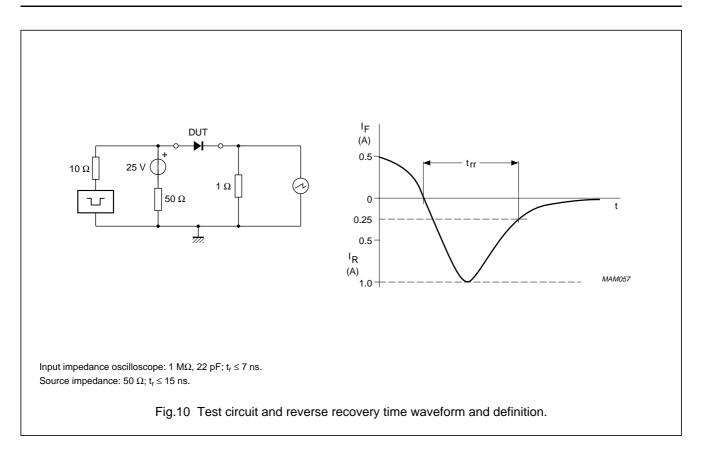






# General purpose controlled avalanche rectifiers

## **BYD17** series



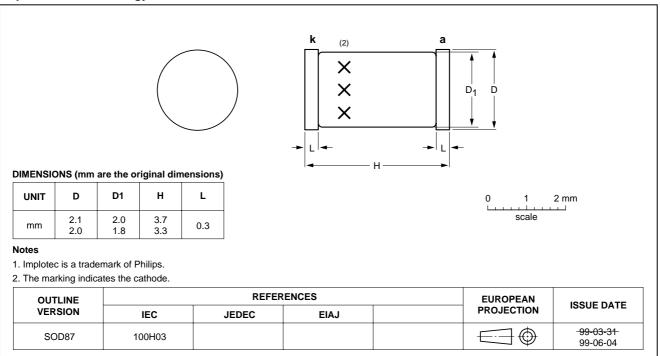
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# General purpose controlled avalanche rectifiers

## **BYD17** series

#### PACKAGE OUTLINE

#### Hermetically sealed glass surface mounted package; Implotec<sup>TM(1)</sup> technology; 2 connectors



#### Product specification

## General purpose controlled avalanche rectifiers

**BYD17** series

#### DATA SHEET STATUS

| DATA SHEET STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITIONS  |
|----------------------------------|----------------------------------|--|
| Objective data                   | Development                      | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.  |
| Preliminary data                 | Qualification                    | This data sheet contains data from the preliminary specification.<br>Supplementary data will be published at a later date. Philips<br>Semiconductors reserves the right to change the specification without<br>notice, in order to improve the design and supply the best possible<br>product.                                     |
| Product data                     | Production                       | This data sheet contains data from the product specification. Philips<br>Semiconductors reserves the right to make changes at any time in order<br>to improve the design, manufacturing and supply. Changes will be<br>communicated according to the Customer Product/Process Change<br>Notification (CPCN) procedure SNW-SQ-650A. |

#### Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

#### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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